

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A method for manufacturing a light emitting device comprising at least one layer of a p-type compound semiconductor layer on an active layer where light is generated and a p-type electrode on the p-type compound semiconductor layer, the method comprising:

forming the p-type compound semiconductor layer on the active layer and annealing twice the resultant structure, wherein annealing twice the resultant structure comprises:

performing first annealing on the resultant structure in a nitrogen atmosphere after the p-type compound semiconductor layer is formed; and

performing second annealing on the first annealed resultant structure in an oxygen atmosphere; and

forming the p-type electrode in direct contact with the twice annealed p-type compound semiconductor layer.

2. (Canceled)

3. (Currently Amended) The method of claim ~~[[2]]~~ 1, wherein the first annealing is performed at an atmospheric pressure at a temperature of 300-1000°C for a duration from 30 seconds to 3 hours.

4. (Currently Amended) The method of claim ~~[[2]]~~ 1, wherein the second annealing is performed at an atmospheric pressure at a temperature of 300-1000°C for a duration from 30 seconds to 3 hours.

5. (Original) The method of claim 1, wherein the p-type electrode is formed as a single layer or a multi-layer.

6. (Original) The method of claim 5, wherein the single layer is formed of a Pd layer, a Ni layer, a Pt layer, or an Au layer.

7. (Original) The method of claim 5, wherein the multi-layer is formed of at least two layers selected from the group consisting of a Pd layer, a Ni layer, a Pt layer, and an Au layer.

8. (Original) The method of claim 1, wherein the p-type compound semiconductor layer is formed of a p-GaN layer.

9. (Original) The method of claim 1, wherein the p-type compound semiconductor layer is formed as a multi-layer, and the uppermost layer of the p-type compound semiconductor layer that contacts the p-type electrode is formed of a p-GaN layer.

10-12. (Canceled)

13. (Currently Amended) A method for manufacturing a light emitting device, the method comprising:

forming at least one layer of n-type compound semiconductor layer on a substrate;

forming an active layer on the n-type compound semiconductor layer, the active layer where light is generated;

forming at least one layer of p-type compound semiconductor layer on the active layer;

annealing twice the resultant structure including the p-type compound semiconductor layer, wherein annealing twice the resultant structure comprises:

performing first annealing on the resultant structure in a nitrogen atmosphere; and

performing second annealing on the first annealed resultant structure in an oxygen atmosphere;

forming a p-type electrode in direct contact with the twice annealed p-type compound semiconductor layer; and

forming an n-type electrode to contact the n-type compound semiconductor layer.

14. (Canceled).

15. (Currently Amended) The method of claim ~~[[14]]~~ 13, wherein the first annealing is performed at an atmospheric pressure at a temperature of 300-1000°C for a duration from 30 seconds to 3 hours.

16. (Currently Amended) The method of claim ~~[[14]]~~ 13, wherein the second annealing is performed at an atmospheric pressure at a temperature of 300-1000°C for a duration from 30 seconds to 3 hours.

17. (Original) The method of claim 13, wherein the p-type electrode is formed as a single layer or a multi-layer.

18. (Original) The method of claim 17, wherein the single layer is formed of a Pd layer, a Ni layer, a Pt layer, or an Au layer.

19. (Original) The method of claim 17, wherein the multi-layer is formed of at least two layers selected from the group consisting of a Pd layer, a Ni layer, a Pt layer, and an Au layer.

20. (Original) The method of claim 13, wherein the p-type compound semiconductor layer is formed of a p-GaN layer.

21. (Original) The method of claim 13, wherein the p-type compound semiconductor layer is formed as a multi-layer, and the uppermost layer of the p-type compound semiconductor layer that contacts the p-type electrode is formed of a p-GaN layer.

22-24. (Canceled)